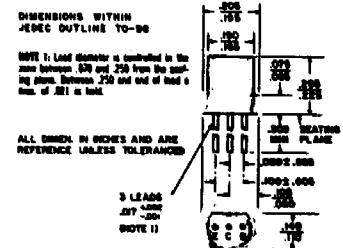


Silicon Transistors



absolute maximum ratings: (25°C) (unless otherwise specified)

Voltages			
Collector to Emitter	V_{CE0}	-40	Volts
Emitter to Base	V_{EB0}	-4	Volts
Collector to Base	V_{CB0}	-40	Volts
Current			
Collector (Continuous)	I_C	300	mA
Collector (Pulsed, 10 μ sec pulse width, = 2% Duty Cycle)	I_C	700	mA
Dissipation			
Total Power (Free Air at 25°C)*	P_T	360	mW
Total Power (Free Air at 55°C)*	P_T	260	mW
Temperature			
Storage	T_{stg}	-65 to +150	°C
Operating	T_j	+125	°C
Lead temperature, 1/16" \pm 1/32" from case for ten seconds maximum	T_L	+260	°C



* Derate 3.6 mW/°C increase in ambient temperature above 25°C.

electrical characteristics: (25°C) (unless otherwise specified)

Static Characteristics		Min.	Max.	
Collector Cutoff Current				
($V_{CB} = -40V$)	I_{CBO}		-100	nA
($V_{CB} = -40V, T_A = 100^\circ C$)	I_{CBO}		-10	μA
($V_{CB} = -40V$)	I_{CES}		-100	nA
Emitter Cutoff Current ($V_{EB} = -4V$)				
	I_{EBO}		-10	μA
Forward Current Transfer Ratio				
($V_{CE} = -10V, I_C = -2 mA$)	2N5365	h_{FE}	32	
($V_{CE} = -1V, I_C = -50 mA$)	2N5365	h_{FE}	40	120
($V_{CE} = -5V, I_C = -300 mA$)	2N5365	h_{FE}	20	
($V_{CE} = -10V, I_C = -2 mA$)	2N5366	h_{FE}	80	
($V_{CE} = -1V, I_C = -50 mA$)	2N5366	h_{FE}	100	300
($V_{CE} = -5V, I_C = -300 mA$)	2N5366	h_{FE}	40	
($V_{CE} = -10V, I_C = -2 mA$)	2N5367	h_{FE}	200	
($V_{CE} = -1V, I_C = -50 mA$)	2N5367	h_{FE}	250	500
($V_{CE} = -5V, I_C = -300 mA$)	2N5367	h_{FE}	75	
Collector Emitter Breakdown Voltage				
($I_C = -10 mA$)	$V_{(BR)CBO}$	-40		Volts
Collector Saturation Voltage				
($I_C = -50 mA, I_B = -2.5 mA$)	$V_{CE(sat)}$		-250	Volts
($I_C = -300 mA, I_B = -30 mA$)	$V_{CE(sat)}$		-1.0	Volts
Base Saturation Voltage				
($I_C = -50 mA, I_B = -2.5 mA$)	$V_{BE(sat)}$		-1.1	Volts
($I_C = -300 mA, I_B = -30 mA$)	$V_{BE(sat)}$		-2.0	Volts
Base Emitter Voltage				
($V_{CB} = -10V, I_C = -2 mA$)	V_{BE}	-0.5	-0.8	Volts